

S3+® memories pass rigorous screening and environmental testing processes. Our modules are designed for a wide range of applications to deliver the best performance at an attractive price.

Description

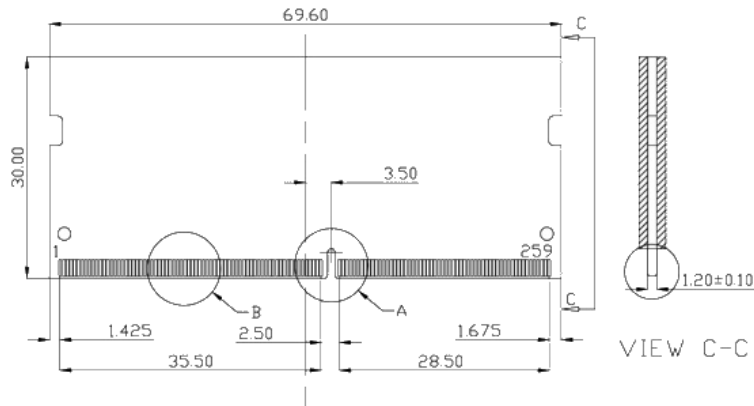
The memory module S3S4N2619041 is a SODIMM 512Mx64-bit (4GB) DDR4-2666 CL19 SDRAM 1RX8, based on eight 512M x 8-bit FBGA components. The SPD is programmed to JEDEC standard latency DDR4-2666 timing of 19-19-19 at 1,2V. This 260-pin SODIMM uses gold contact fingers.

Features

- Power Supply: VDD = 1,2V Typical
- VDDQ = 1,2V Typical
- VPP = 2,5V Typical
- VDDSPD = 2,2V to 3,6V
- Nominal and dynamic on-die termination (ODT) for data, strobe, and mask signals
- Low-power auto self refresh (LPASR)
- Single-rank
- 8 internal banks; 2 groups of 4 banks each
- Fixed burst chop (BC) of 4 and burst length (BL) of 8 via the mode register set (MRS)
- Selectable BC4 or BL8 on-the-fly (OTF)
- Fly-by topology
- PCB: Height 1,18" (30mm)
- RoHS Compliant and Halogen-Free



Module Dimensions



Specifications

Total Capacity	4GB
Form Factor	SODIMM
ECC	NON-ECC
CL (IDD)	19 cycles
Row Cycle Time (tRCmin)	45.75ns(min.)
Refresh to Active/Refresh Command Time (tRFCmin)	350ns(min.)
Row Active Time (tRASmin)	32ns(min.)
Maximum Operating Power	TBD W*
UL Rating	94 V - 0
Operating Temperature	0° C to +85° C
Storage Temperature	-55° C to +100° C

*Power will vary depending on the SDRAM used.